

FSAM75SM60A

SPM™ (Smart Power Module)

General Description

FSAM75SM60A is an advanced smart power module (SPM) that Fairchild has newly developed and designed to provide very compact and low cost, yet high performance ac motor drives mainly targeting medium speed low-power inverter-driven application like air conditioners. It combines optimized circuit protection and drive matched to low-loss IGBTs. Highly effective short-circuit current detection/protection is realized through the use of advanced current sensing IGBT chips that allow continuous monitoring of the IGBTs current. System reliability is further enhanced by the built-in over-temperature and integrated under-voltage lock-out protection. The high speed built-in HVIC provides opto-coupler-less IGBT gate driving capability that further reduce the overall size of the inverter system design. In addition the incorporated HVIC facilitates the use of single-supply drive topology enabling the FSAM75SM60A to be driven by only one drive supply voltage without negative bias. Inverter current sensing application can be achieved due to the devided negative dc terminals.

Features

- UL Certified No. E209204
- 600V-75A 3-phase IGBT inverter bridge including control ICs for gate driving and protection
- Divided negative dc-link terminals for inverter current sensing applications
- Single-grounded power supply due to built-in HVIC
- Typical switching frequency of 5kHz
- Built-in thermistor for over-temperature monitoring
- Isolation rating of 2500Vrms/min.
- Very low leakage current due to using DBC (Direct Bonded Copper) substrate
- Adjustable current protection level by varying series resistor value with sense-IGBTs

Applications

- AC 100V ~ 253V three-phase inverter drive for small power ac motor drives
- Home appliances applications like air conditioners drive system

External View

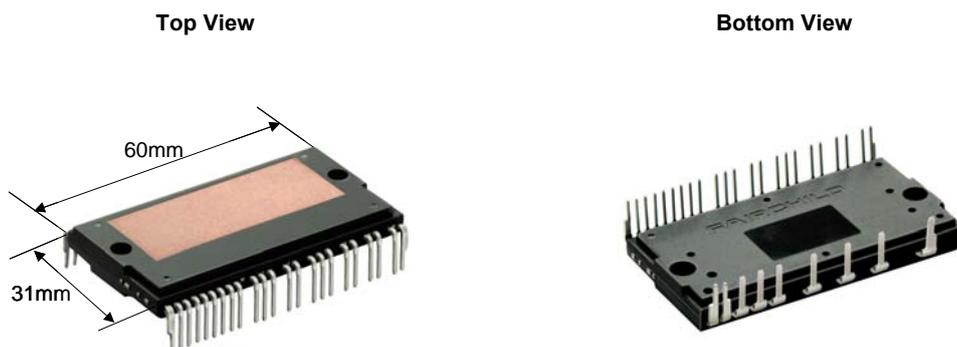


Fig. 1.

Integrated Power Functions

- 600V-75A IGBT inverter for three-phase DC/AC power conversion (Please refer to Fig. 3)

Integrated Drive, Protection and System Control Functions

- For inverter high-side IGBTs: Gate drive circuit, High voltage isolated high-speed level shifting
Control circuit under-voltage (UV) protection
Note) Available bootstrap circuit example is given in Figs. 13 and 14.
- For inverter low-side IGBTs: Gate drive circuit, Short circuit protection (SC)
Control supply circuit under-voltage (UV) protection
- Temperature Monitoring: System over-temperature monitoring using built-in thermistor
Note) Available temperature monitoring circuit is given in Fig. 14.
- Fault signaling: Corresponding to a SC fault (Low-side IGBTs) or a UV fault (Low-side control supply circuit)
- Input interface: 5V CMOS/LSTTL compatible, Schmitt trigger input

Pin Configuration

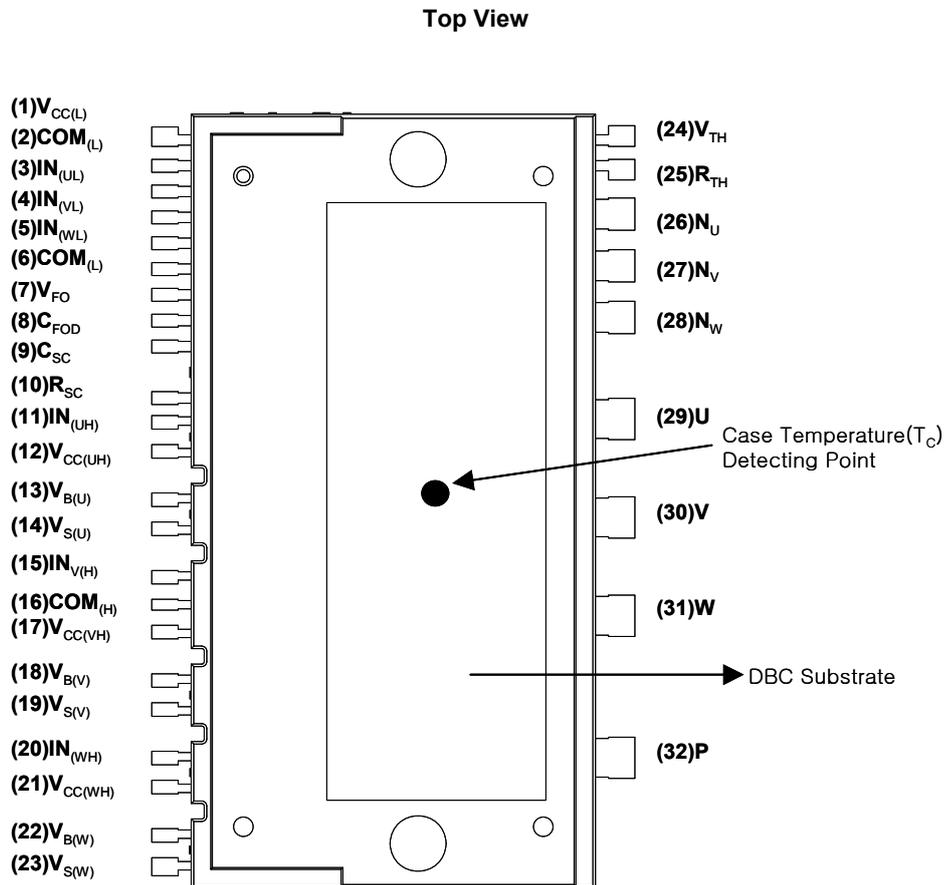
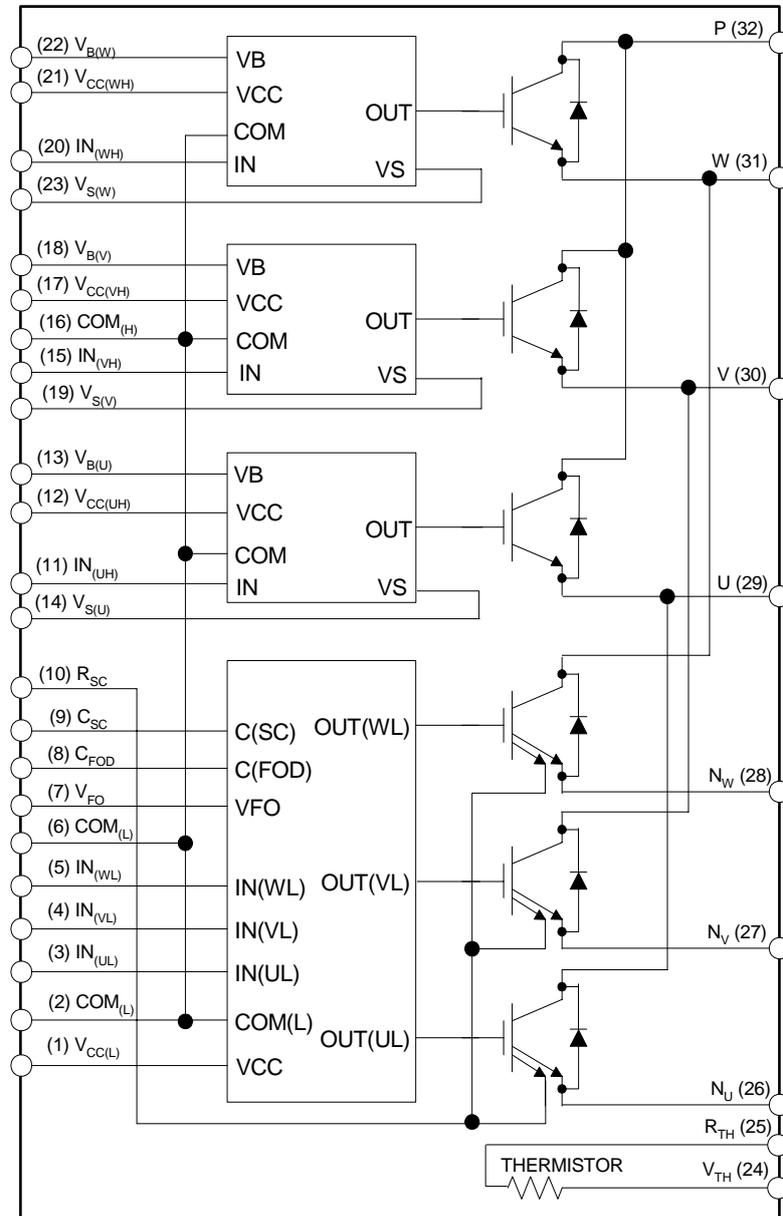


Fig. 2.

Pin Descriptions

Pin Number	Pin Name	Pin Description
1	$V_{CC(L)}$	Low-side Common Bias Voltage for IC and IGBTs Driving
2	$COM_{(L)}$	Low-side Common Supply Ground
3	$IN_{(UL)}$	Signal Input Terminal for Low-side U Phase
4	$IN_{(VL)}$	Signal Input Terminal for Low-side V Phase
5	$IN_{(WL)}$	Signal Input Terminal for Low-side W Phase
6	$COM_{(L)}$	Low-side Common Supply Ground
7	V_{FO}	Fault Output
8	C_{FOD}	Capacitor for Fault Output Duration Time Selection
9	C_{SC}	Capacitor (Low-pass Filter) for Short-Circuit Current Detection Input
10	R_{SC}	Resistor for Short-circuit Current Detection
11	$IN_{(UH)}$	Signal Input for High-side U Phase
12	$V_{CC(UH)}$	High-side Bias Voltage for U Phase IC
13	$V_{B(U)}$	High-side Bias Voltage for U Phase IGBT Driving
14	$V_{S(U)}$	High-side Bias Voltage Ground for U Phase IGBT Driving
15	$IN_{(VH)}$	Signal Input for High-side V Phase
16	$COM_{(H)}$	High-side Common Supply Ground
17	$V_{CC(VH)}$	High-side Bias Voltage for V Phase IC
18	$V_{B(V)}$	High-side Bias Voltage for V Phase IGBT Driving
19	$V_{S(V)}$	High-side Bias Voltage Ground for V Phase IGBT Driving
20	$IN_{(WH)}$	Signal Input for High-side W Phase
21	$V_{CC(WH)}$	High-side Bias Voltage for W Phase IC
22	$V_{B(W)}$	High-side Bias Voltage for W Phase IGBT Driving
23	$V_{S(W)}$	High-side Bias Voltage Ground for W Phase IGBT Driving
24	V_{TH}	Thermistor Bias Voltage
25	R_{TH}	Series Resistor for the Use of Thermistor (Temperature Detection)
26	N_U	Negative DC-Link Input Terminal for U Phase
27	N_V	Negative DC-Link Input Terminal for V Phase
28	N_W	Negative DC-Link Input Terminal for W Phase
29	U	Output for U Phase
30	V	Output for V Phase
31	W	Output for W Phase
32	P	Positive DC-Link Input

Internal Equivalent Circuit and Input/Output Pins



Note

1. Inverter low-side is composed of three sense-IGBTs including freewheeling diodes for each IGBT and one control IC which has gate driving, current sensing and protection functions.
2. Inverter power side is composed of four inverter dc-link input pins and three inverter output pins.
3. Inverter high-side is composed of three normal-IGBTs including freewheeling diodes and three drive ICs for each IGBT.

Fig. 3.

Absolute Maximum Ratings (T_J = 25°C, Unless Otherwise Specified)

Inverter Part

Item	Symbol	Condition	Rating	Unit
Supply Voltage	V _{DC}	Applied to DC - Link	450	V
Supply Voltage (Surge)	V _{PN(Surge)}	Applied between P- N	500	V
Collector-emitter Voltage	V _{CES}		600	V
Each IGBT Collector Current	± I _C	T _C = 25°C	75	A
Each IGBT Collector Current	± I _C	T _C = 100°C	37	A
Each IGBT Collector Current (Peak)	± I _{CP}	T _C = 25°C, Under 1ms pulse width	110	A
Collector Dissipation	P _C	T _C = 25°C per One Chip	189	W
Operating Junction Temperature	T _J	(Note 1)	-20 ~ 125	°C

Note

1. It would be recommended that the average junction temperature should be limited to T_J ≤ 125°C (@T_C ≤ 100°C) in order to guarantee safe operation.

Control Part

Item	Symbol	Condition	Rating	Unit
Control Supply Voltage	V _{CC}	Applied between V _{CC(UH)} , V _{CC(VH)} , V _{CC(WH)} - COM _(H) , V _{CC(L)} - COM _(L)	20	V
High-side Control Bias Voltage	V _{BS}	Applied between V _{B(U)} - V _{S(U)} , V _{B(V)} - V _{S(V)} , V _{B(W)} - V _{S(W)}	20	V
Input Signal Voltage	V _{IN}	Applied between IN _(UH) , IN _(VH) , IN _(WH) - COM _(H) , IN _(UL) , IN _(VL) , IN _(WL) - COM _(L)	-0.3 ~ V _{CC} +0.3	V
Fault Output Supply Voltage	V _{FO}	Applied between V _{FO} - COM _(L)	-0.3 ~ V _{CC} +0.3	V
Fault Output Current	I _{FO}	Sink Current at V _{FO} Pin	5	mA
Current Sensing Input Voltage	V _{SC}	Applied between C _{SC} - COM _(L)	-0.3 ~ V _{CC} +0.3	V

Total System

Item	Symbol	Condition	Rating	Unit
Self Protection Supply Voltage Limit (Short Circuit Protection Capability)	V _{PN(PROT)}	Applied to DC - Link, V _{CC} = V _{BS} = 13.5 ~ 16.5V, T _J = 125°C, Non-repetitive, less than 5μs	400	V
Module Case Operation Temperature	T _C	Note Fig. 2	-20 ~ 100	°C
Storage Temperature	T _{STG}		-20 ~ 125	°C
Isolation Voltage	V _{ISO}	60Hz, Sinusoidal, AC 1 minute, Connection Pins to Heat-sink Plate	2500	V _{rms}

Absolute Maximum Ratings

Thermal Resistance

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Junction to Case Thermal Resistance	$R_{th(j-c)Q}$	Inverter IGBT part (per 1/6 module)	-	-	0.56	°C/W
	$R_{th(j-c)F}$	Inverter FWDi part (per 1/6 module)	-	-	0.98	°C/W
Contact Thermal Resistance	$R_{th(c-f)}$	Ceramic Substrate (per 1 Module) Thermal Grease Applied (Note 3)	-	-	0.06	°C/W

Note

- For the measurement point of case temperature(T_C), please refer to Fig. 2.
- The thickness of thermal grease should not be more than 100um.

Package Marking and Ordering Information

Device Marking	Device	Package	Real Size	Tape Width	Quantity
FSAM75SM60A	FSAM75SM60A	SPM32-DA	-	-	8

Electrical Characteristics

Inverter Part ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Collector - emitter Saturation Voltage	$V_{CE(SAT)}$	$V_{CC} = V_{BS} = 15V$ $V_{IN} = 0V$ $I_C = 50A, T_J = 25^\circ\text{C}$	-	-	2.4	V
FWDi Forward Voltage	V_{FM}	$V_{IN} = 5V$ $I_C = 50A, T_J = 25^\circ\text{C}$	-	-	2.1	V
Switching Times	t_{ON}	$V_{PN} = 300V, V_{CC} = V_{BS} = 15V$ $I_C = 75A, T_J = 25^\circ\text{C}$ $V_{IN} = 5V \leftrightarrow 0V$, Inductive Load (High-Low Side) (Note 4)	-	0.76	-	μs
	$t_{C(ON)}$		-	0.44	-	μs
	t_{OFF}		-	1.42	-	μs
	$t_{C(OFF)}$		-	0.46	-	μs
	t_{rr}		-	0.10	-	μs
Collector - emitter Leakage Current	I_{CES}	$V_{CE} = V_{CES}, T_J = 25^\circ\text{C}$	-	-	250	μA

Note

- t_{ON} and t_{OFF} include the propagation delay time of the internal drive IC. $t_{C(ON)}$ and $t_{C(OFF)}$ are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Fig. 4.

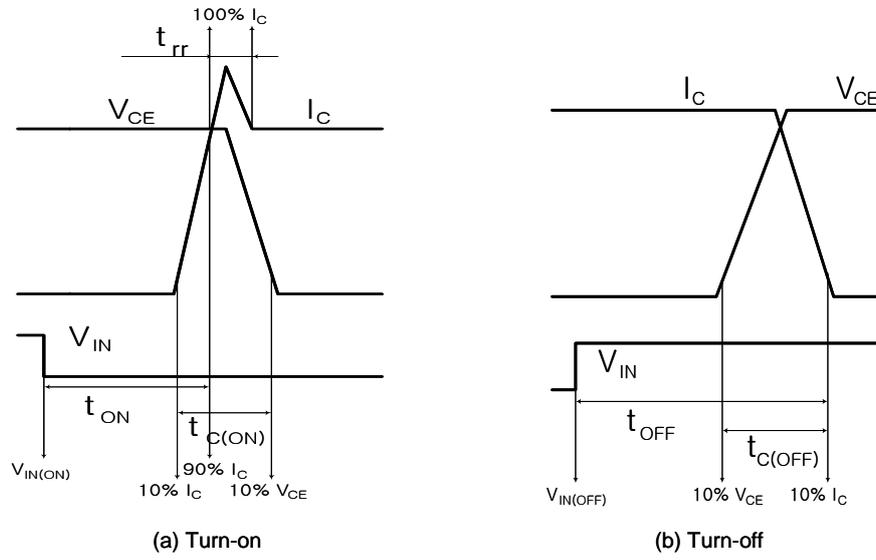


Fig. 4. Switching Time Definition

Electrical Characteristics (T_J = 25°C, Unless Otherwise Specified)

Control Part

Item	Symbol	Condition	Min.	Typ.	Max.	Unit		
Quiescent V _{CC} Supply Current	I _{QCCL}	V _{CC} = 15V IN _(UL, VL, WL) = 5V	V _{CC(L)} - COM _(L)	-	-	26	mA	
	I _{QCCH}	V _{CC} = 15V IN _(UH, VH, WH) = 5V	V _{CC(UH)} , V _{CC(VH)} , V _{CC(WH)} - COM _(H)	-	-	130	uA	
Quiescent V _{BS} Supply Current	I _{QBS}	V _{BS} = 15V IN _(UH, VH, WH) = 5V	V _{B(U)} - V _{S(U)} , V _{B(V)} - V _{S(V)} , V _{B(W)} - V _{S(W)}	-	-	420	uA	
Fault Output Voltage	V _{FOH}	V _{SC} = 0V, V _{FO} Circuit: 4.7kΩ to 5V Pull-up	4.5	-	-	V		
	V _{FOL}	V _{SC} = 1V, V _{FO} Circuit: 4.7kΩ to 5V Pull-up	-	-	1.1	V		
Short-Circuit Trip Level	V _{SC(ref)}	V _{CC} = 15V (Note 5)	0.45	0.51	0.56	V		
Sensing Voltage of IGBT Current	V _{SEN}	R _{SC} = 26 Ω, R _{SU} = R _{SV} = R _{SW} = 0 Ω and I _C = 100A (Fig. 6)	0.45	0.51	0.56	V		
Supply Circuit Under-Voltage Protection	UV _{CCD}	Detection Level	11.5	12	12.5	V		
	UV _{CCR}	Reset Level	12	12.5	13	V		
	UV _{BSD}	Detection Level	7.3	9.0	10.8	V		
	UV _{BSR}	Reset Level	8.6	10.3	12	V		
Fault Output Pulse Width	t _{FOD}	C _{FOD} = 33nF (Note 6)	1.4	1.8	2.0	ms		
ON Threshold Voltage	V _{IN(ON)}	High-Side	Applied between IN _(UH) , IN _(VH) , IN _(WH) - COM _(H)		-	-	0.8	V
OFF Threshold Voltage	V _{IN(OFF)}		3.0	-	-	V		
ON Threshold Voltage	V _{IN(ON)}	Low-Side	Applied between IN _(UL) , IN _(VL) , IN _(WL) - COM _(L)		-	-	0.8	V
OFF Threshold Voltage	V _{IN(OFF)}		3.0	-	-	V		
Resistance of Thermistor	R _{TH}	@ T _{TH} = 25°C (Note Fig. 5) (Note 7)	-	50	-	kΩ		
		@ T _{TH} = 100°C (Note Fig. 5) (Note 7)	-	3.0	-	kΩ		

Note:

- Short-circuit current protection is functioning only at the low-sides. It would be recommended that the value of the external sensing resistor (R_{SC}) should be selected around 26 Ω in order to make the SC trip-level of about 100A at the shunt resistors (R_{SU}, R_{SV}, R_{SW}) of 0Ω. For the detailed information about the relationship between the external sensing resistor (R_{SC}) and the shunt resistors (R_{SU}, R_{SV}, R_{SW}), please see Fig. 6.
- The fault-out pulse width t_{FOD} depends on the capacitance value of C_{FOD} according to the following approximate equation : C_{FOD} = 18.3 x 10⁻⁶ x t_{FOD}[F]
- T_{TH} is the temperature of thermistor itself. To know case temperature (T_C), please make the experiment considering your application.

Recommended Operating Conditions

Item	Symbol	Condition	Values			Unit
			Min.	Typ.	Max.	
Supply Voltage	V _{PN}	Applied between P - N _U , N _V , N _W	-	300	400	V
Control Supply Voltage	V _{CC}	Applied between V _{CC(UH)} , V _{CC(VH)} , V _{CC(WH)} - COM _(H) , V _{CC(L)} - COM _(L)	13.5	15	16.5	V
High-side Bias Voltage	V _{BS}	Applied between V _{B(U)} - V _{S(U)} , V _{B(V)} - V _{S(V)} , V _{B(W)} - V _{S(W)}	13.0	15	18.5	V
Blanking Time for Preventing Arm-short	t _{dead}	For Each Input Signal	3.5	-	-	us
PWM Input Signal	f _{PWM}	T _C ≤ 100°C, T _J ≤ 125°C	-	5	-	kHz
Minimum Input Pulse Width	PW _{IN(OFF)}	200 ≤ V _{PN} ≤ 400V, 13.5 ≤ V _{CC} ≤ 16.5V, 13.0 ≤ V _{BS} ≤ 18.5V, 0 ≤ I _C ≤ 110A, -20 ≤ T _J ≤ 125°C V _{IN} = 5V ↔ 0V, Inductive Load (Note 8)	3	-	-	us
Input ON Threshold Voltage	V _{IN(ON)}	Applied between IN _(UH) , IN _(VH) , IN _(WH) - COM _(H) , IN _(UL) , IN _(VL) , IN _(WL) - COM _(L)	0 ~ 0.65			V
Input OFF Threshold Voltage	V _{IN(OFF)}	Applied between IN _(UH) , IN _(VH) , IN _(WH) - COM _(H) , IN _(UL) , IN _(VL) , IN _(WL) - COM _(L)	4 ~ 5.5			V

Note:

- SPM might not make response if the PW_{IN(OFF)} is less than the recommended minimum value.

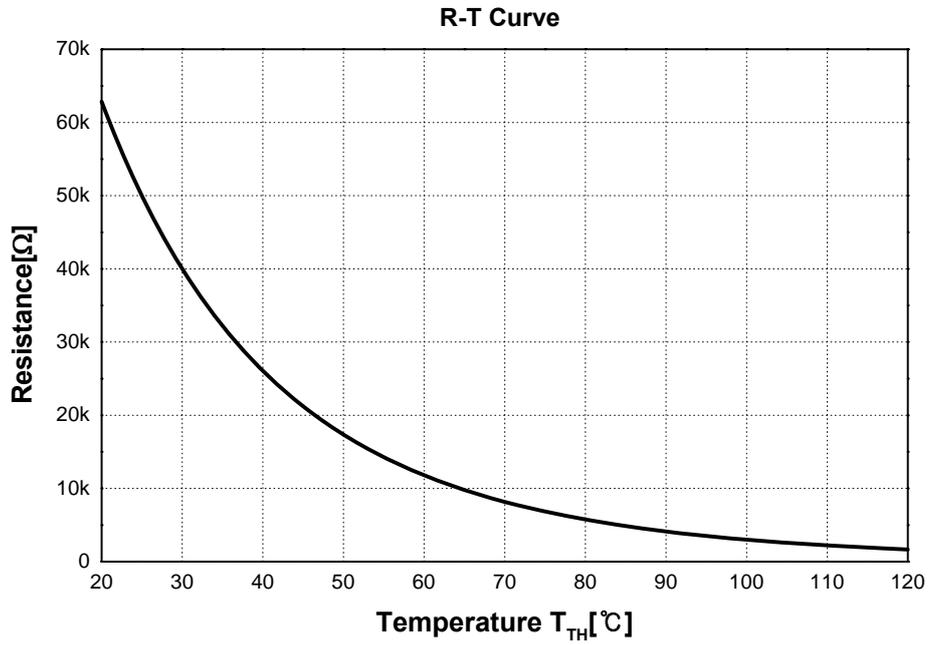


Fig. 5. R-T Curve of The Built-in Thermistor

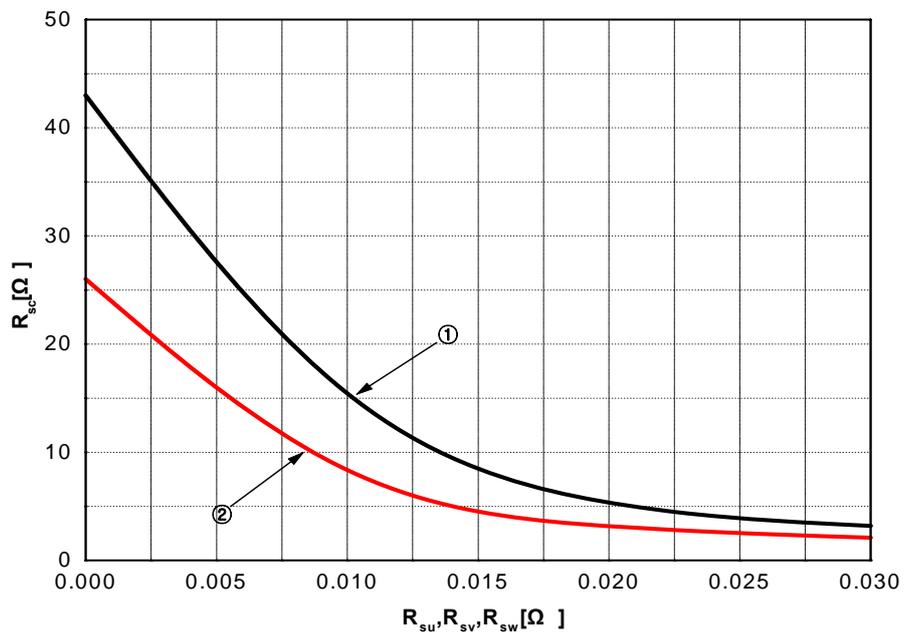


Fig. 6. R_{SC} Variation by change of Shunt Resistors (R_{SU} , R_{SV} , R_{SW}) for Short-Circuit Protection
 ① @ Current Trip Level \approx 75A,
 ② @ Current Trip Level \approx 100A

Mechanical Characteristics and Ratings

Item	Condition	Limits			Units	
		Min.	Typ.	Max.		
Mounting Torque	Mounting Screw: M4 (Note 9 and 10)	Recommended 10Kg•cm	8	10	12	Kg•cm
		Recommended 0.98N•m	0.78	0.98	1.17	N•m
DBC Flatness	Note Fig.7	0	-	+120	μm	
Weight		-	32	-	g	

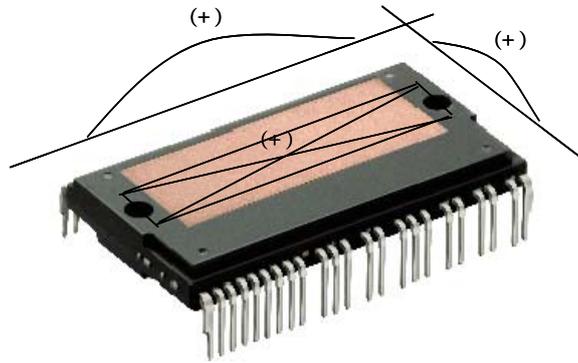


Fig. 7. Flatness Measurement Position of The DBC Substrate

Note:

- 9. Do not make over torque or mounting screws. Much mounting torque may cause ceramic cracks and bolts and Al heat-fin destruction.
- 10. Avoid one side tightening stress. Fig.8 shows the recommended torque order for mounting screws. Uneven mounting can cause the SPM ceramic substrate to be damaged.

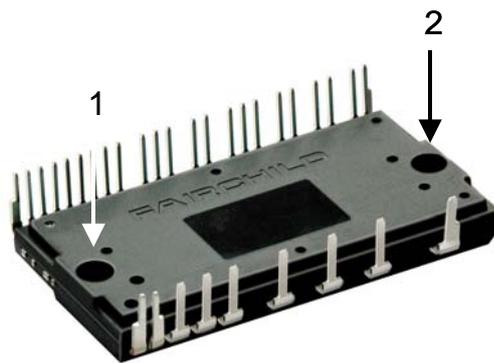
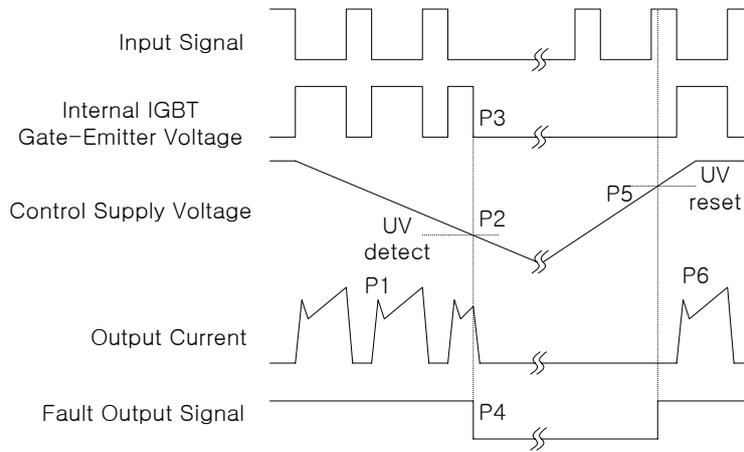


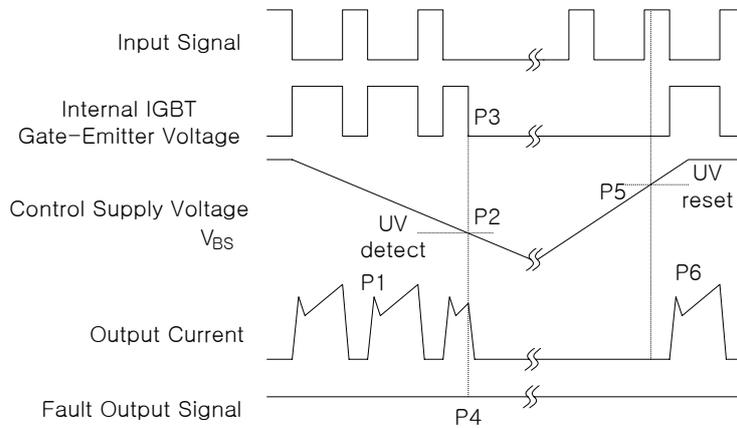
Fig. 8. Mounting Screws Torque Order (1 → 2)

Time Charts of SPMs Protective Function



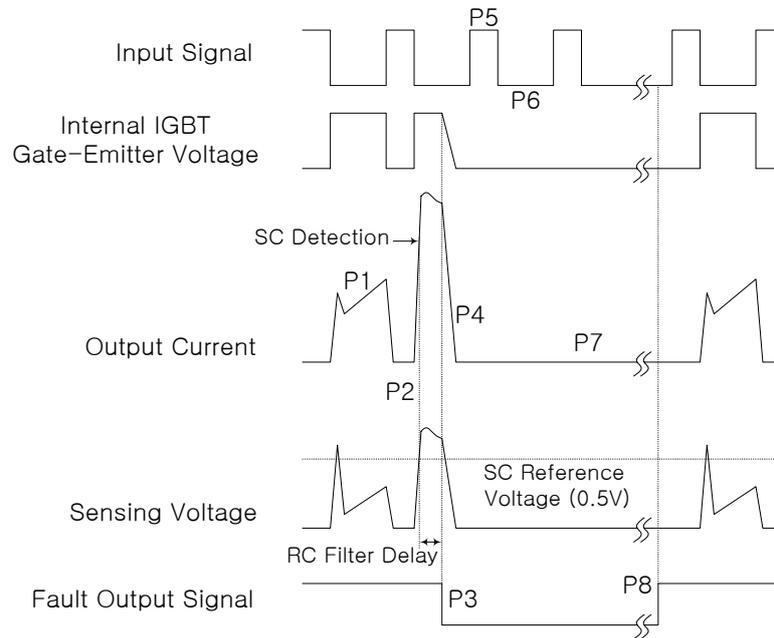
- P1 : Normal operation - IGBT ON and conducting current
- P2 : Under voltage detection
- P3 : IGBT gate interrupt
- P4 : Fault signal generation
- P5 : Under voltage reset
- P6 : Normal operation - IGBT ON and conducting current

Fig. 9. Under-Voltage Protection (Low-side)



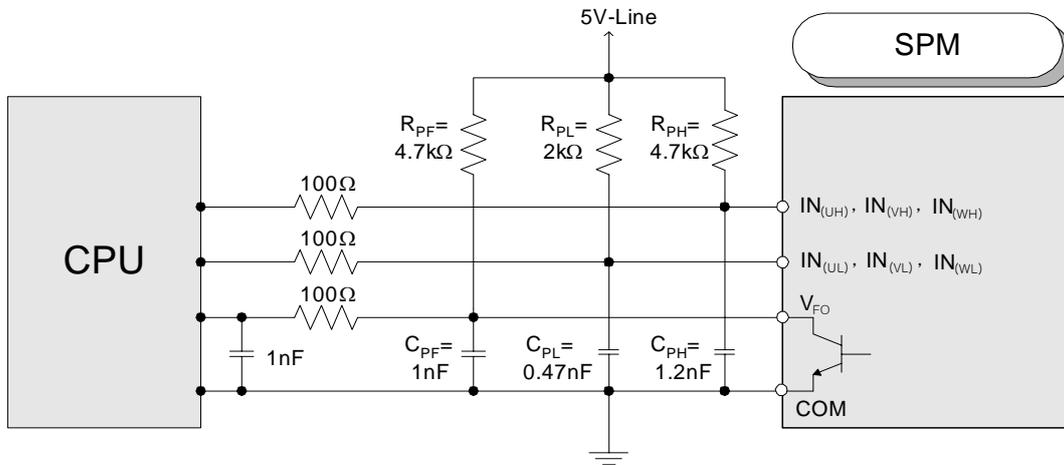
- P1 : Normal operation - IGBT ON and conducting current
- P2 : Under voltage detection
- P3 : IGBT gate interrupt
- P4 : No fault signal
- P5 : Under voltage reset
- P6 : Normal operation - IGBT ON and conducting current

Fig. 10. Under-Voltage Protection (High-side)



- P1 : Normal operation - IGBT ON and conducting currents
- P2 : Short-circuit current detection
- P3 : IGBT gate interrupt / Fault signal generation
- P4 : IGBT is slowly turned off
- P5 : IGBT OFF signal
- P6 : IGBT ON signal - but IGBT cannot be turned on during the fault-output activation
- P7 : IGBT OFF state
- P8 : Fault-output reset and normal operation start

Fig. 11. Short-circuit Current Protection (Low-side Operation only)

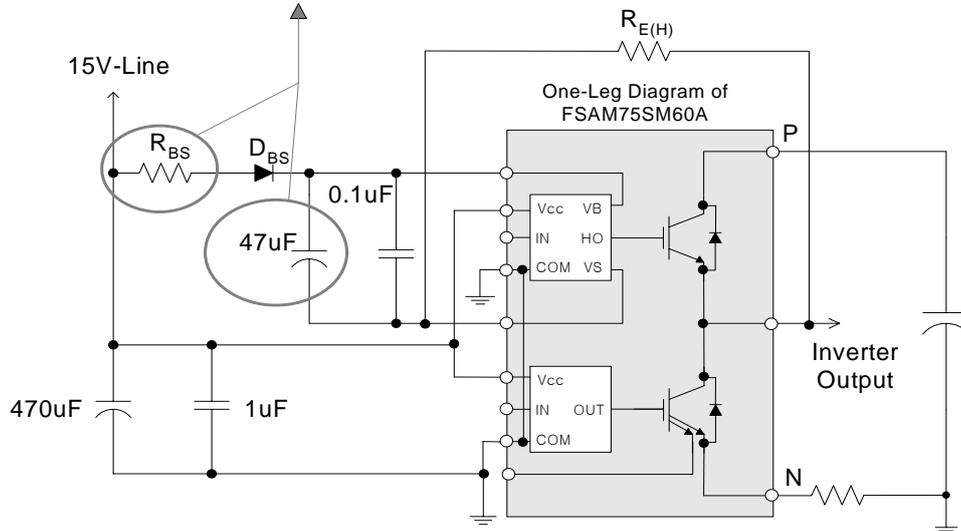


Note:

- 1) It would be recommended that by-pass capacitors for the gating input signals, $IN_{(UL)}$, $IN_{(VL)}$, $IN_{(WL)}$, $IN_{(UH)}$, $IN_{(VH)}$ and $IN_{(WH)}$ should be placed on the SPM pins and on the both sides of CPU and SPM for the fault output signal, V_{FO} , as close as possible.
- 2) The logic input is compatible with standard CMOS or LSTTL outputs.
- 3) $R_{PL}C_{PL}/R_{PH}C_{PH}/R_{PF}C_{PF}$ coupling at each SPM input is recommended in order to prevent input/output signals' oscillation and it should be as close as possible to each of SPM pins.

Fig. 12. Recommended CPU I/O Interface Circuit

These Values depend on PWM Control Algorithm



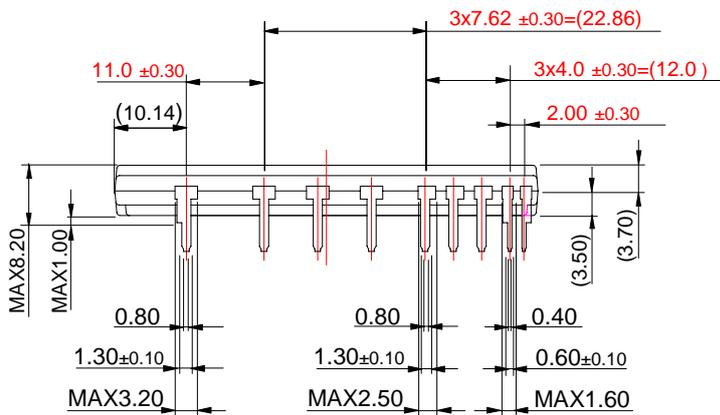
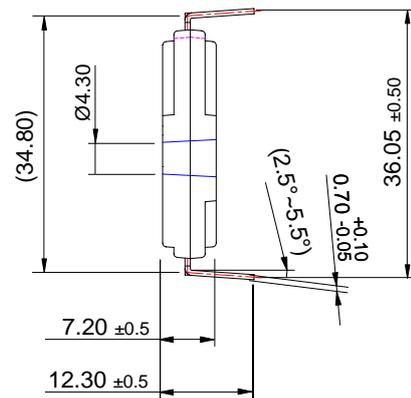
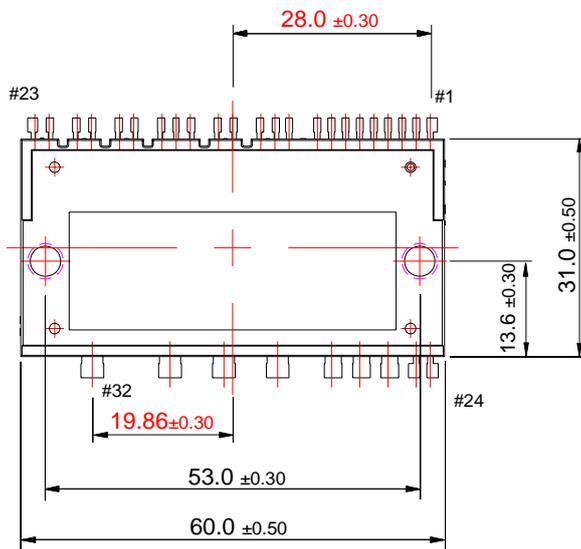
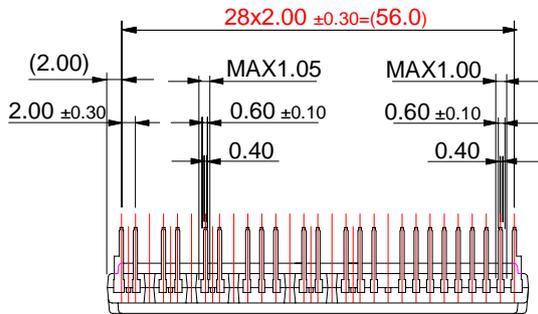
Note:

- 1) It would be recommended that the bootstrap diode, D_{BS} , has soft and fast recovery characteristics.
- 2) The bootstrap resistor (R_{BS}) should be 3 times greater than $R_{E(H)}$. The recommended value of $R_{E(H)}$ is 5.6Ω , but it can be increased up to 20Ω for a slower dv/dt of high-side.
- 3) The ceramic capacitor placed between V_{CC} -COM should be over $1\mu F$ and mounted as close to the pins of the SPM as possible.

Fig. 13. Recommended Bootstrap Operation Circuit and Parameters

Detailed Package Outline Drawings

SPM32-DA



Dimensions in Millimeters

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ACE _x ™	FAST®	PACMAN™	SuperSOT™-3
Bottomless™	FAST _r ™	POP™	SuperSOT™-6
CoolFET™	GlobalOptoisolator™	PowerTrench®	SuperSOT™-8
CROSSVOLT™	GTO™	QFET™	SyncFET™
DenseTrench™	HiSeC™	QS™	TinyLogic™
DOME™	ISOPLANAR™	QT Optoelectronics™	UHC™
EcoSPARK™	LittleFET™	Quiet Series™	UltraFET®
E2CMOS™	MicroFET™	SLIENT SWITCHER®	VCX™
EnSigna™	MICROWIRE™	SMART START™	
FACT™	OPTOLOGIC™	Star* Power™	
FACT Quiet Series™	OPTOPLANAR™	Stealth™	

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PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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